



PRODUCT DATA SHEET

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Datasheet



Resources



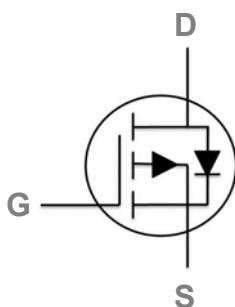
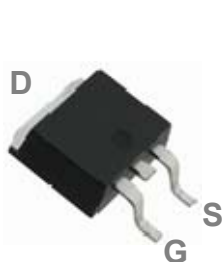
Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

TO252



BVDSS	RDSON	ID
-100V	210mΩ	-10A

Features

- -100V, -10A, $R_{DS(ON)}$ 210mΩ@VGS = -10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _C =25°C)	-10	A
	Drain Current – Continuous (T _C =100°C)	-6.5	A
I _{DM}	Drain Current – Pulsed ¹	-40	A
P _D	Power Dissipation (T _C =25°C)	54	W
	Power Dissipation – Derate above 25°C	0.43	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 125	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance Junction to Case	---	2.3	°C/W
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	---	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-80V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-5A	---	170	210	mΩ
		V _{GS} =-4.5V, I _D =-2A	---	190	230	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1	---	-3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =-3A	---	7	---	S

Dynamic and switching Characteristics

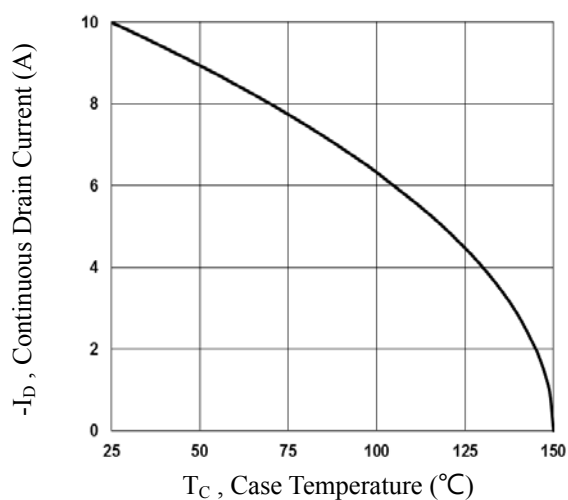
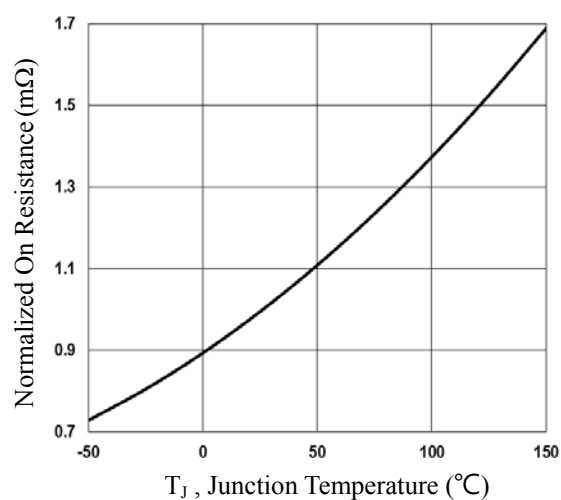
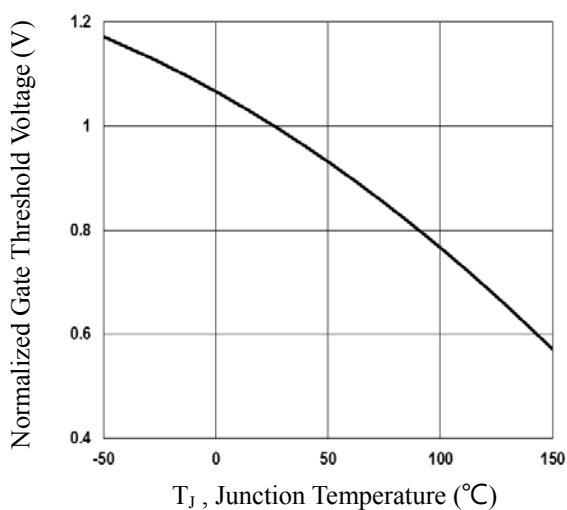
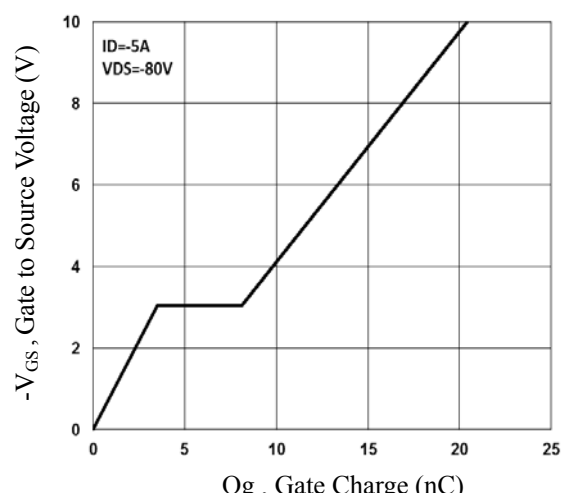
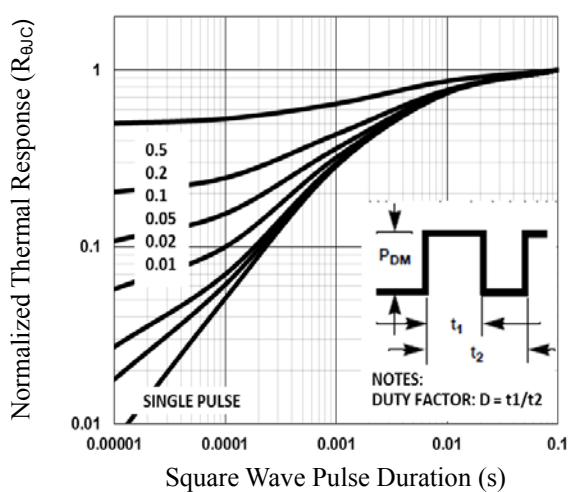
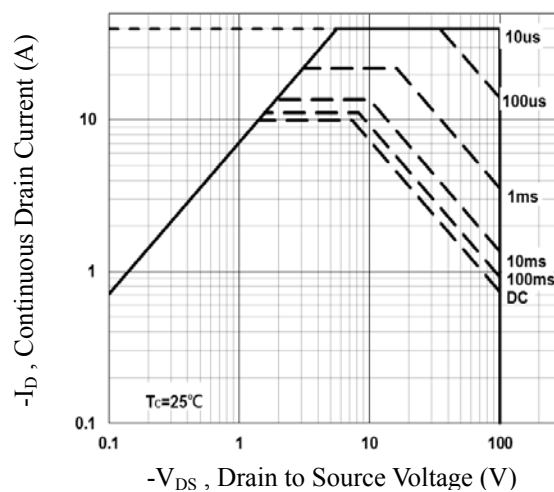
Q _g	Total Gate Charge	V _{DS} =-80V, V _{GS} =-10V, I _D =-5A	---	20	40	nC
Q _{gs}	Gate-Source Charge		---	3.5	7	
Q _{gd}	Gate-Drain Charge		---	4.6	9	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V, V _{GS} =-10V, R _G =25Ω I _D =-5A	---	18	36	ns
T _r	Rise Time		---	8	16	
T _{d(off)}	Turn-Off Delay Time		---	100	200	
T _f	Fall Time		---	30	60	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, F=1MHz	---	1419	2500	pF
C _{oss}	Output Capacitance		---	89	170	
C _{rss}	Reverse Transfer Capacitance		---	45	90	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	16	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-10	A
I _{SM}	Pulsed Source Current		---	---	-20	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time ²	V _{GS} =0V, I _S =-5A, dI/dt=100A/μs	---	26.6	---	ns
Q _{rr}	Reverse Recovery Charge ²	T _J =25°C	---	24.2	---	uC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.


Fig.1 Continuous Drain Current vs. T_c

Fig.2 Normalized RDSON vs. T_J

Fig.3 Normalized V_{th} vs. T_J

Fig.4 Gate Charge Waveform

Fig.5 Normalized Transient Impedance

Fig.6 Maximum Safe Operation Area

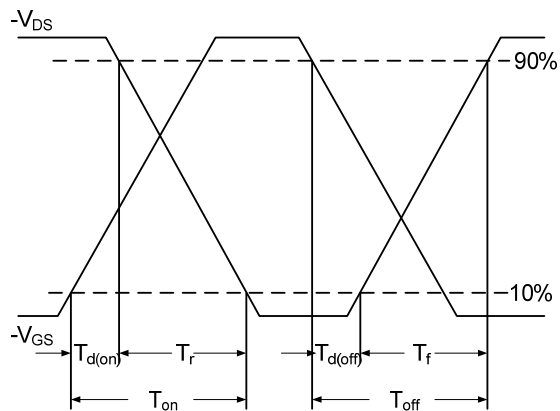


Fig.7 Switching Time Waveform

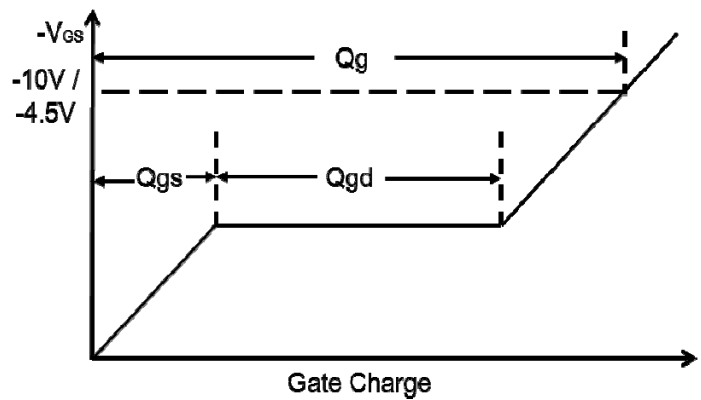
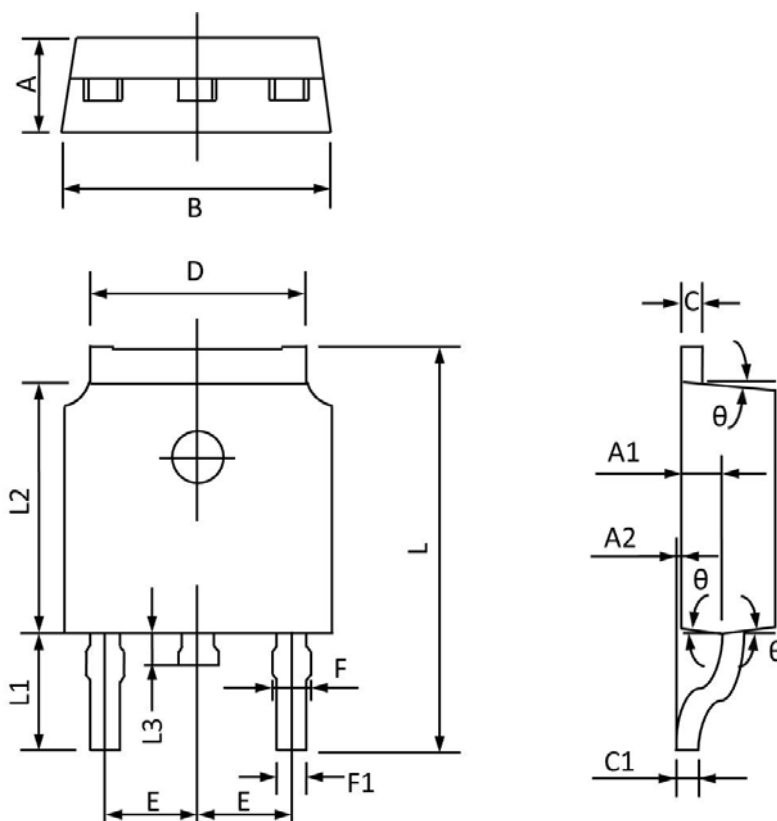


Fig.8 Gate Charge Waveform

TO252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.20	2.40	0.087	0.094
A1	0.91	1.11	0.036	0.044
A2	0.00	0.15	0.000	0.006
B	6.50	6.70	0.256	0.264
C	0.46	0.580	0.018	0.230
C1	0.46	0.580	0.018	0.030
D	5.10	5.46	0.201	0.215
E	2.186	2.386	0.086	0.094
F	0.74	0.94	0.029	0.037
F1	0.660	0.860	0.026	0.034
L	9.80	10.40	0.386	0.409
L1	2.9REF		0.114REF	
L2	6.00	6.20	0.236	0.244
L3	0.60	1.00	0.024	0.039
θ	3°	9°	3°	9°

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